



## Description

The HXY50P03BD uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = -30V$   $I_D = 50A$

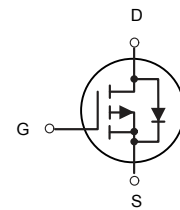
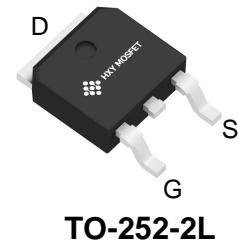
$R_{DS(ON)} < 18m\Omega$  @  $V_{GS}=10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY50P03BD	TO-252-2L	HXY 50P03BD xxxxxx	2500

## Absolute Maximum Ratings ( $T_c=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS}$ @ -10V	-50	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS}$ @ -10V	-32	A
$I_{DM}$	Pulsed Drain Current	-150	A
EAS	Single Pulse Avalanche Energy	125	mJ
$I_{AS}$	Avalanche Current	-50	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	45	W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^{\circ}C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	62	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	2.8	$^{\circ}C/W$



### Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T$	BVDSS Temperature Coefficient	Reference to $25^{\circ}\text{C}$ , $I_D=-1\text{mA}$	---	-0.0232	---	V/ $^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-10V$ , $I_D=-30A$	---	15	18	$m\Omega$
		$V_{GS}=-4.5V$ , $I_D=-15A$	---	24	32	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=-250\mu A$	-1.0	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	mV/ $^{\circ}\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-24V$ , $V_{GS}=0V$ , $T_J=25^{\circ}\text{C}$	---	---	-1	$\mu A$
		$V_{DS}=-24V$ , $V_{GS}=0V$ , $T_J=55^{\circ}\text{C}$	---	---	-5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 25V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=-5V$ , $I_D=-30A$	---	30	---	S
$R_g$	Gate Resistance	$V_{DS}=0V$ , $V_{GS}=0V$ , $f=1\text{MHz}$	---	9	---	$\Omega$
$Q_g$	Total Gate Charge (-4.5V)	$V_{DS}=-15V$ , $V_{GS}=-4.5V$ , $I_D=-15A$	---	22	---	nC
$Q_{gs}$	Gate-Source Charge		---	8.7	---	
$Q_{gd}$	Gate-Drain Charge		---	7.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$ , $V_{GS}=-10V$ , $R_G=3.3\Omega$ $I_D=-15A$	---	8	---	ns
$T_r$	Rise Time		---	73.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	61.8	---	
$T_f$	Fall Time		---	24.4	---	
$C_{iss}$	Input Capacitance	$V_{DS}=-15V$ , $V_{GS}=0V$ , $f=1\text{MHz}$	---	2215	---	pF
$C_{oss}$	Output Capacitance		---	310	---	
$C_{rss}$	Reverse Transfer Capacitance		---	237	---	

### Diode Characteristics

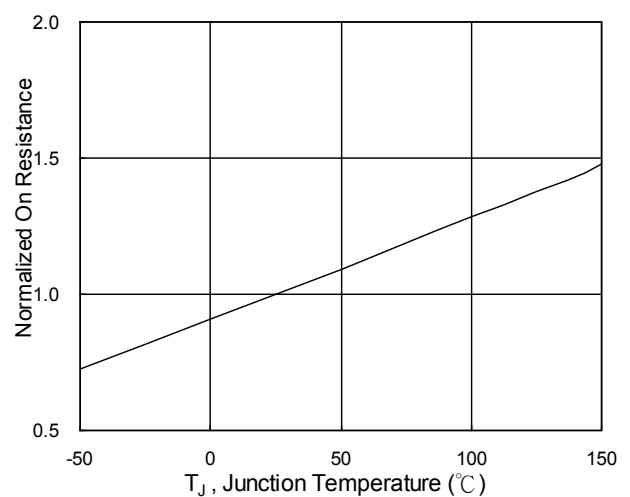
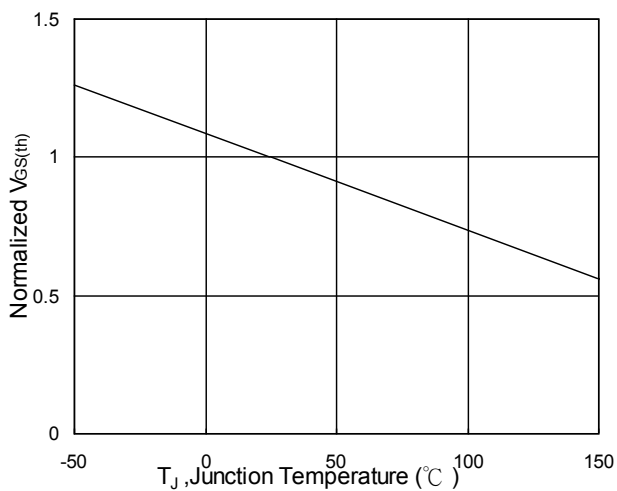
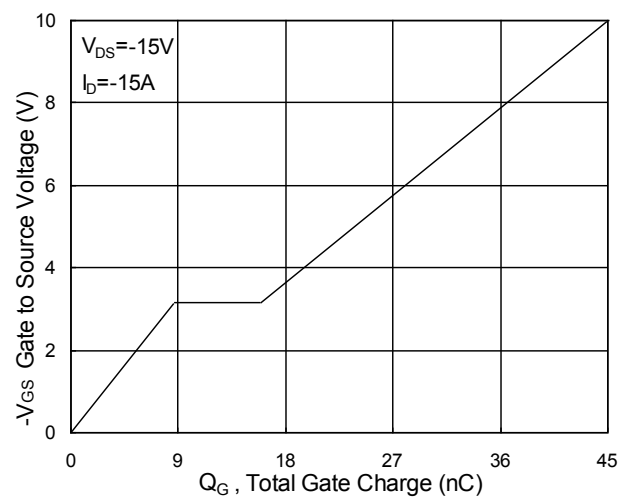
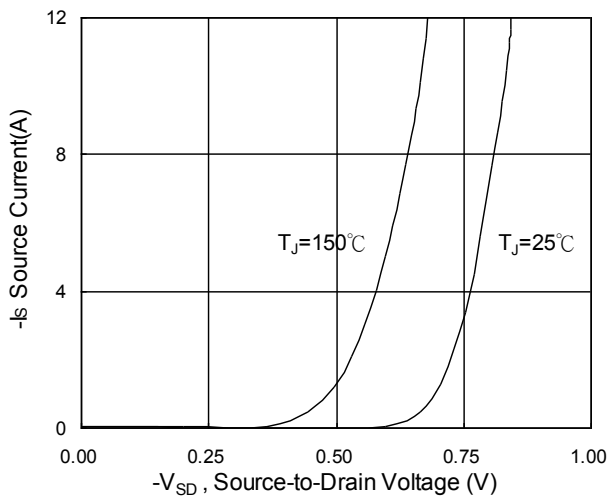
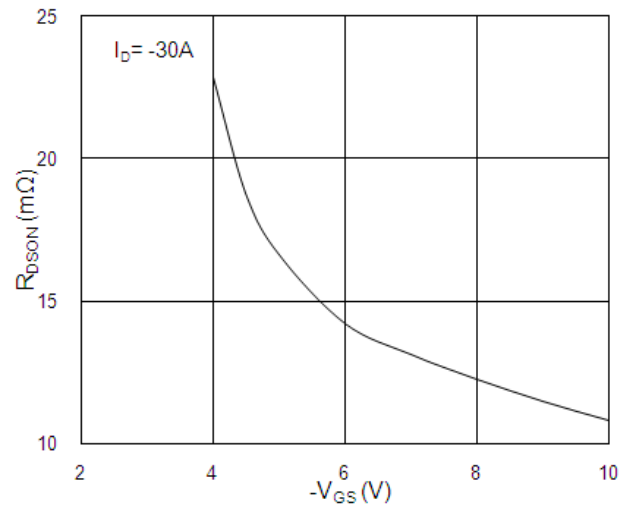
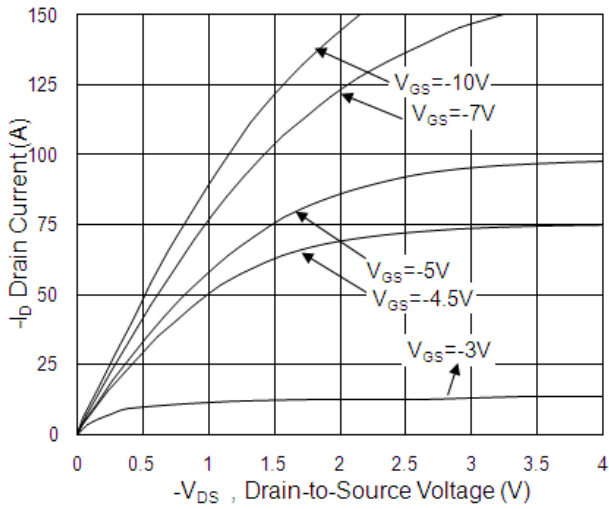
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V$ , Force Current	---	---	-50	A
$I_{SM}$	Pulsed Source Current <sup>2,5</sup>		---	---	-150	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V$ , $I_S=-1A$ , $T_J=25^{\circ}\text{C}$	---	---	-1	V
$t_{rr}$	Reverse Recovery Time	$I_F=-15A$ , $di/dt=100A/\mu s$ , $T_J=25^{\circ}\text{C}$	---	19	---	nS
$Q_{rr}$	Reverse Recovery Charge	$T_J=25^{\circ}\text{C}$	---	9	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=-25V$ ,  $V_{GS}=-10V$ ,  $L=0.1mH$ ,  $I_{AS}=-50A$
- 4.The power dissipation is limited by  $150^{\circ}\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



## Typical Characteristics



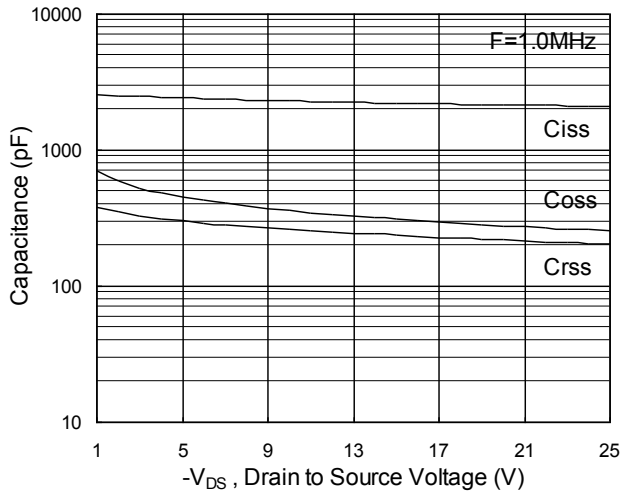


Fig.7 Capacitance

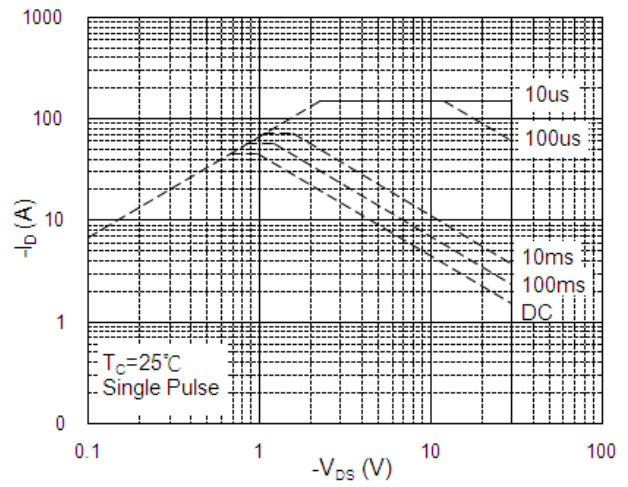


Fig.8 Safe Operating Area

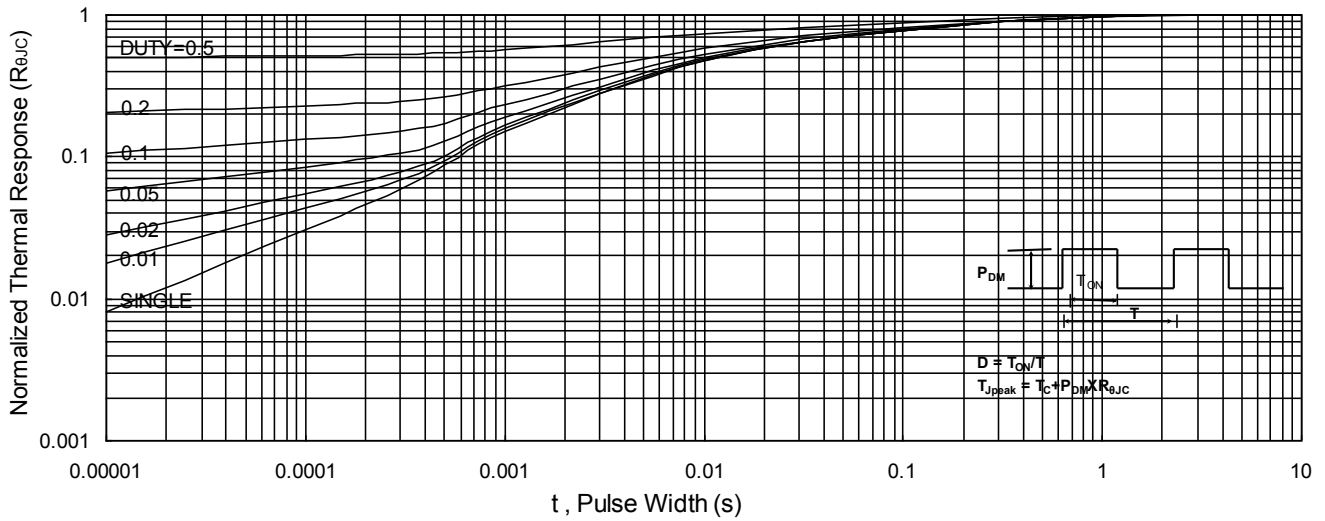


Fig.9 Normalized Maximum Transient Thermal Impedance

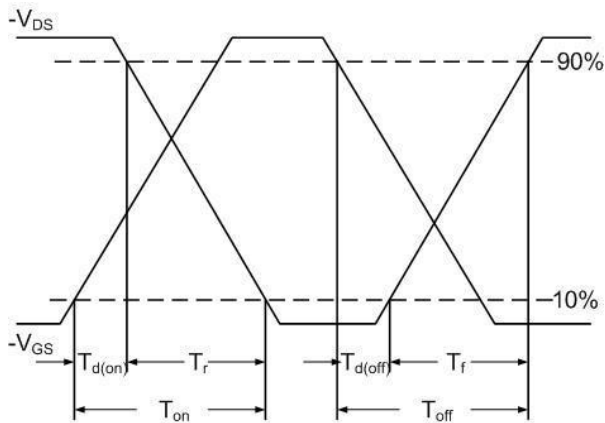


Fig.10 Switching Time Waveform

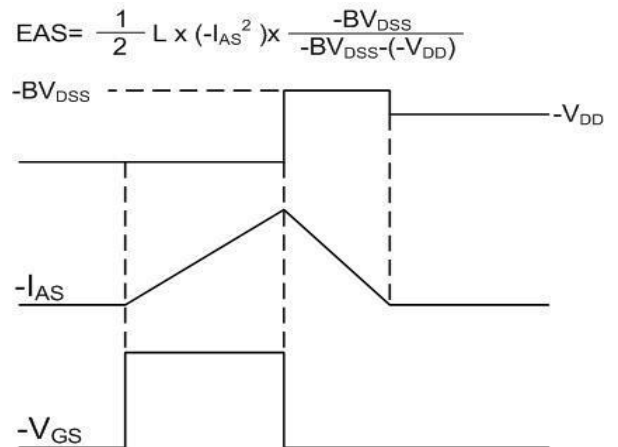
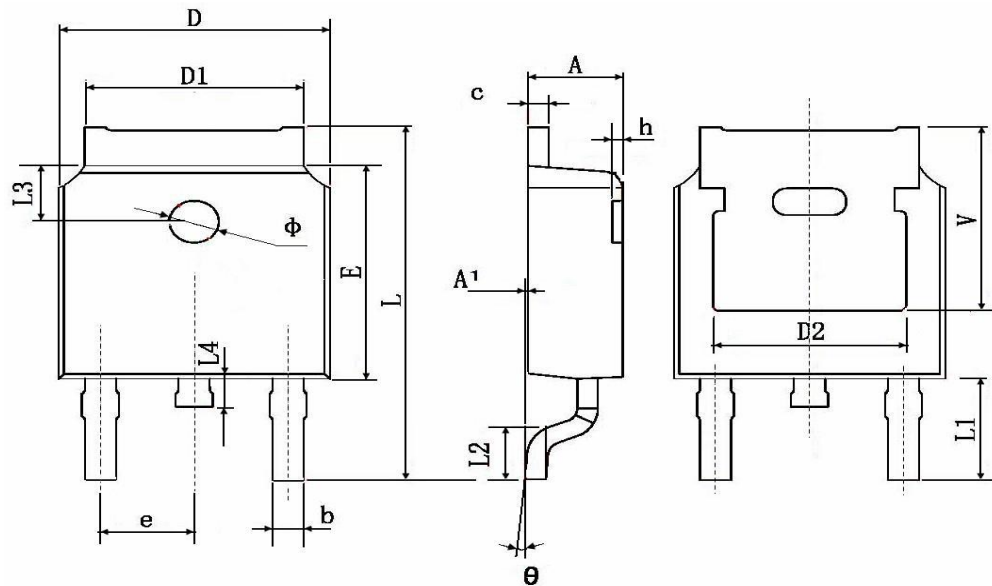


Fig.11 Unclamped Inductive Switching Waveform



## TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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